

Characteristics ($T_j = 25^\circ\text{C}$)
Kennwerte ($T_j = 25^\circ\text{C}$)

		Min.	Typ.	Max.
Collector-Base cutoff current – Kollektor-Basis-Reststrom $V_{CB} = 25\text{ V}$, (E open)		–	–	100 nA
Emitter-Base cutoff current – Emitter-Basis-Reststrom $V_{EB} = 4\text{ V}$, (C open)		–	–	100 nA
Transition Frequency – Transitfrequenz $V_{CE} = 5\text{ V}$, $I_C = 50\text{ mA}$, $f = 100\text{ MHz}$		–	170 MHz	–
Collector-Base Capacitance – Kollektor-Basis-Kapazität $V_{CB} = 10\text{ V}$, $I_E = i_e = 0$, $f = 1\text{ MHz}$		–	3 pF	–
Thermal resistance junction to soldering point Wärmewiderstand Sperrschicht – Löt看点		< 70 K/W		
Recommended complementary PNP transistors Empfohlene komplementäre PNP-Transistoren		BC807K / BC808K		
Marking of available current gain groups per type Stempelung der lieferbaren Stromverstärkungsgruppen pro Typ	BC817K-16 = 6A or 6CR BC817K-25 = 6B or 6CS BC817K-40 = 6C or 6CT	BC818K-16 = 6E or 6CR BC818K-25 = 6F or 6CS BC818K-40 = 6G or 6CT		